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**INFORMATION DISCLOSURE  
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Application Number	10/634,174
Filing Date	August 5, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2823
Examiner Name	Garcia, Joannie

Attorney Docket No: 1303.102US1

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Examiner Initials *	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published.		T <sup>4</sup>
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Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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